# Photoluminescence property of 15R-sialon:Eu<sup>2+</sup> phosphors and their XANES spectra

Shinichi KIKKAWA<sup>\*1</sup>, Yuji Masubuchi<sup>1</sup>, Teruki MOTOHASHI<sup>1</sup>, Takashi TAKEDA<sup>2</sup>, Kei-ichiro MURAI<sup>3</sup> and Akira YOSHIASA<sup>4</sup> <sup>1</sup>Hokkaido Univ., Sapporo 060-8628, Japan <sup>2</sup>NIMS, Tsukuba 305-0044, Japan <sup>3</sup>Tokushima Univ., Tokushima 770-8506, Japan <sup>4</sup>Kumamoto Univ., Kumamoto 860-8555, Japan

## **Introduction**

Sialon ceramics are the most widely studied and used high temperature structural materials over the past many years. Recently, both  $\alpha$ - and  $\beta$ -sialons have been used as host materials for RE cations to give luminescence, e.g., Ca- $\alpha$ -sialon:Eu<sup>2+</sup> [1] and  $\beta$ -sialon:Eu<sup>2+</sup> (green) [2]. The luminescence allows sialon materials to find new functional applications in displays and white lightemitting diodes (LEDs), due to superior thermal and chemical stabilities.

In addition to the  $\alpha$ - and  $\beta$ -sialons, there are other types of sialon phases. It is well known that in the phase diagram of Si<sub>3</sub>N<sub>4</sub>, SiO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, and AlN, at the compositions between  $\beta$ -sialon and AlN, there are several AlN-polytypoid phases, e.g., 8H, 15R, 12H, 21R, 27R and 2H. In our preliminary study, Eu<sup>2+</sup> doped 15R-sialon powders prepared by gel nitridation and post-annealing were found to exhibit a blue light emission under 254nm excitation [3]. However, the phase pure Eu<sup>2+</sup> doped 15R sialon has not been obtained, and effect of Eu concentration on the luminescence was also not studied.

In this study,  $Eu^{2+}$  doped 15R-sialon (SiAl<sub>4</sub>O<sub>2</sub>N<sub>4</sub>) was synthesized from the powder mixture of Si<sub>3</sub>N<sub>4</sub>, SiO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, AlN, and Eu<sub>2</sub>O<sub>3</sub> by gas-pressure sintering, and photoluminescence property was discussed with Eu valency.

### **Experimental**

The raw powders were homogeneously mixed with ethanol, and the mixtures were fired in a gas pressure sintering furnace at 1800°C for 3h under a nitrogen pressure of 0.5MPa. The Eu concentration was varied from 0 to 1.5mol% with respect to 15R-sialon.

Phase identification was conducted by powder X-ray diffraction (XRD). Photoluminescence property was measured by a spectrofluorometer. X-ray absorption of Eu  $L_{III}$ -edge was measured in transmission mode at the beam line 9C in Photon Factory.

## **Results and discussion**

The formation of 15R-sialon was observed after gas pressure sintering at 1800°C. At 0 and 0.05 mol% Eu, in addition to the major 15R phase, two kinds of impurities  $\beta$ -sialon and AlN were observed. At 0.1 and 0.5 mol% Eu,

the impurity was only the residual AlN. When the Eu concentration increased to 1 mol% and above, single phase of 15R-sialon was formed without these impurities. These Eu doped 15R phases exhibit broad blue emission spectra with maximum at 445 nm and a shoulder at about 465nm under UV light excitation.

Figure 1 shows Eu  $L_{III}$ -edge XANES spectra of the synthesize 15R phase with various Eu contents. All products contained both Eu<sup>2+</sup> and Eu<sup>3+</sup>. The ratio of Eu<sup>2+</sup>/Eu<sup>3+</sup> increases with increasing Eu contents. However, no Eu<sup>3+</sup> emission (line spectra around 620nm) was observed in PL measurement. These results indicate that a part of Eu<sup>2+</sup> enter into the 15R-sialon phase resulting in the broad blue emission. Eu<sup>3+</sup> might form a liquid phase during the sintering, and remain as an amorphous phase. The two emission peaks suggest that there are two kinds of Eu<sup>2+</sup> site having difference coordination environment.



Fig. 1 Eu LIII-edge XANES spectra of Eu doped 15Rsialon products and references.

#### References

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\*kikkawa@eng.hokudai.ac.jp